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SC10776P D01

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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)		Complete If Known	
		Application Number	101007754
		Filing Date	
		First Named Inventor	Darrell G. Hill
		Group Art Unit	
		Examiner Name	
Sheet 2 of 2	Attorney Docket Number	SC10776P C01	

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T*
VAMJ	19	H. Lin et al., "Super-Gain AlGaAs/GaAs Heterojunction Bipolar Transistors Using An Emitter Edge-Thinning Design", American Institute of Physics, appl. Phys. Letter 47(8), 15 October 1985, pages 839-841.	
VAMJ	20	W. Lee et al., "Effect of Emitter-Base Spacing on the current Gain of AlGaAs/GaAs Heterojunction Bipolar Transistors", IEEE Electronic Device Letters, Vol. 10, No. 5, May 1989, pages 200-202.	
VAMJ	21	Wolf, S., "Silicon Processing for the VLSI Era, Volume 2", Process Integration, Sunset Beach, CA, 1990, pages 486-488.	

Examiner Signature	Victor H. Mandala Jr	Date Considered	8-30-04
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation, if not in conformance and not considered. Include copy of this form with next communication to applicant.

\* Unique citation designation number. \* Applicant is to place a check mark here if English Language Translation is attached.